ABSTRACT OF THE DISCLOSURE

Disclosed is a semiconductor laser light emitting device including: a stacked film composed of a stack of group III nitride semiconductor films each containing at least one kind selected from aluminum, gallium, indium, and boron; wherein an upper portion of the stacked film is formed into a ridge-like stripe, to form a current injection region; a current non-injection region formed on both sides of the ridge-like stripe; and at least part of the current non-injection region is made from a material expressed by a chemical formula $Al_xGa_{1-x}N$ ($0 \leqq x \leqq 1.0$). In this device, the component ratio "x" of Al is specified at a value in a range of $0.3 \leqq x \leqq 1.0$, so that the semiconductor laser light emitting device is configured as an index guide type semiconductor laser light emitting device; the component ratio "x" of Al is specified at a value in a range of $0.15 < x < 0.30$, so that the semiconductor laser light emitting device is configured as a weak index type pulsation semiconductor laser light emitting device; or the component ratio "x" of Al is specified at a value in a range of $0 \leqq x \leqq 0.15$, so that the semiconductor laser light emitting device is configured as a gain guide type laser light emitting device.